

6367254 MOTOROLA SC (XSTRS/R F)

96D 80590

DT-33-15

T-33-23

**MOTOROLA SEMICONDUCTOR TECHNICAL DATA**

**NPN  
BD315, BD316  
PNP  
BD317, BD318**

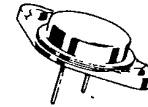
**COMPLEMENTARY SILICON HIGH-POWER TRANSISTORS**

... designed for high quality amplifiers operating up to 100 Watts into 4 ohm load with BD315, BD316 and into 8 ohm load with BD317, BD318.

- High DC Current Gain
- Excellent Safe Operating Area
- High Current Gain — Bandwidth Product — Typical  
 $f_T = 2.0 \text{ MHz} @ I_C = 1.0 \text{ A}$

**16 AMPERE  
COMPLEMENTARY SILICON  
POWER TRANSISTORS**

**80-100 VOLTS  
200 WATTS**



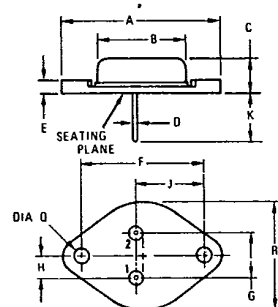
**MAXIMUM RATINGS**

Rating	Symbol	BD315 BD316	BD317 BD318	Unit
Collector-Emitter Voltage	$V_{CEO}$	80	100	Vdc
Collector-Base Voltage	$V_{CB}$	80	100	Vdc
Emitter-Base Voltage	$V_{EB}$	7.0		Vdc
Collector Current — Continuous	$I_C$	16	20	Adc
Collector Current — Peak				
Base Current — Continuous	$I_B$	5.0		Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	200	1.14	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200		$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$\theta_{JC}$	0.875	$^\circ\text{C/W}$

3



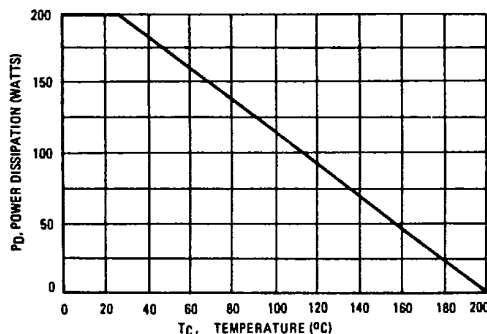
STYLE 1  
PIN 1 BASE  
2 EMITTER  
CASE COLLECTOR  
NOTE  
1 DIM "D" IS DIA

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A		39.37		1.560
B		21.08		0.830
C	5.35	7.62	0.250	0.300
D	0.99	1.05	0.039	0.043
E		3.43		0.135
F	29.90	30.40	1.177	1.197
G	10.67	11.18	0.420	0.440
H	5.33	5.59	0.210	0.220
J	16.64	17.15	0.655	0.675
K	11.18	12.19	0.440	0.480
Q	3.84	4.09	0.151	0.161
R		26.67		1.050

Collector connected to case

CASE 11 (TO-3)

FIGURE 1 — POWER DERATING



6367254 MOTOROLA SC (XSTRS/R F)  
 BD315, BD316, BD317, BD318

96D 80591 D

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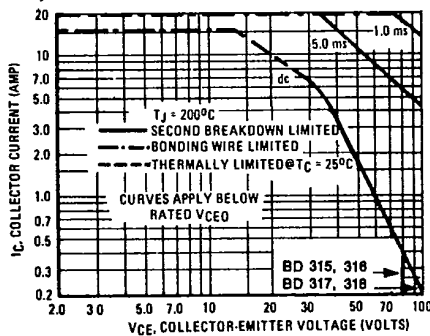
\* ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Sustaining Voltage (1) ( $I_C = 200 \text{ mAdc}$ , $I_B = 0$ )	BD315, BD316 BD317, BD318 $V_{CE(sus)}$	80 100	— —	Vdc
Collector-Base Cutoff Current ( $V_{CB} = \text{Rated } V_{CB}$ , $I_E = 0$ )	$I_{CBO}$	—	1.0	mAdc
Emitter-Base Cutoff Current ( $V_{EB} = 7.0 \text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	—	1.0	mAdc
<b>ON CHARACTERISTICS (1)</b>				
DC Current Gain $I_C = 5.0 \text{ Adc}$ , $V_{CE} = 4.0 \text{ Vdc}$ $I_C = 8.0 \text{ Adc}$ , $V_{CE} = 4.0 \text{ Vdc}$ $I_C = 10 \text{ Adc}$ , $V_{CE} = 4.0 \text{ Vdc}$	BD317, BD318 BD315, BD316 All Types $h_{FE}$	25 25 15	—	—
Collector-Emitter Saturation Voltage $I_C = 8.0 \text{ Adc}$ , $I_B = 0.8 \text{ Adc}$	$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage $I_C = 8.0 \text{ Adc}$ , $I_B = 0.8 \text{ Adc}$	$V_{BE(sat)}$	—	1.8	Vdc
Base-Emitter On Voltage ( $I_C = 8.0 \text{ Adc}$ , $V_{CE} = 2.0 \text{ Vdc}$ )	$V_{BE(on)}$	—	1.5	Vdc
<b>DYNAMIC CHARACTERISTICS</b>				
Current-Gain—Bandwidth Product (2) ( $I_C = 1.0 \text{ Adc}$ , $V_{CE} = 20 \text{ Vdc}$ , $f_{test} = 0.5 \text{ MHz}$ )	$f_T$	1.0	—	MHz

(1) Pulse Test: Pulse Width  $< 300 \mu\text{s}$ , Duty Cycle  $> 2.0\%$ .  
 (2)  $f_T = |h_{FE}| \cdot f_{test}$ .



FIGURE 2 — ACTIVE REGION SAFE OPERATING AREA



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on  $T_{J(pk)} = 200^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 200^\circ\text{C}$ . At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. (See AN-415).

6367254 MOTOROLA SC (XSTRS/R F)

96D 80592 D

BD315, BD316, BD317, BD318

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PNP DEVICES  
BD316 and BD318

NPN DEVICES  
BD315 and BD317

FIGURE 3 — DC CURRENT GAIN

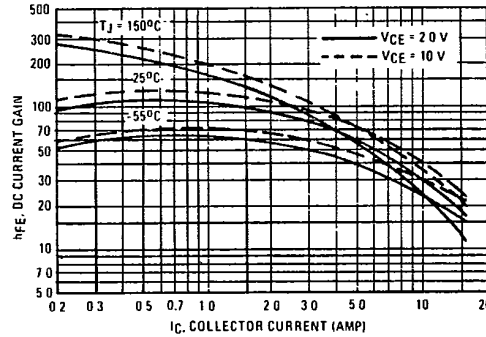
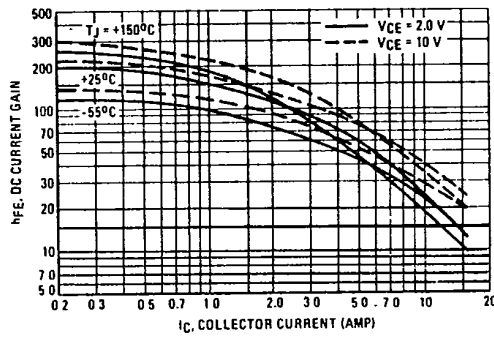
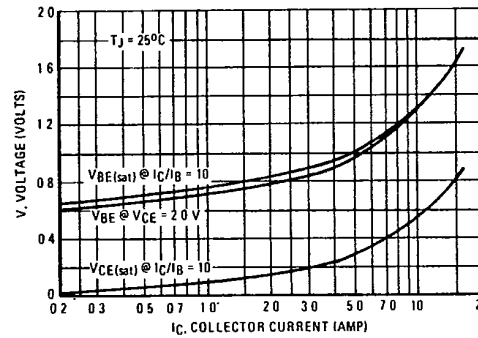
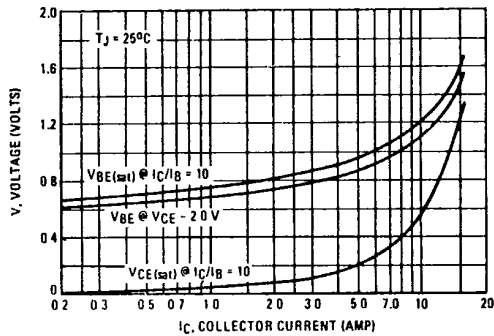


FIGURE 4 — "ON" VOLTAGES





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